



SEMICONDUCTOR

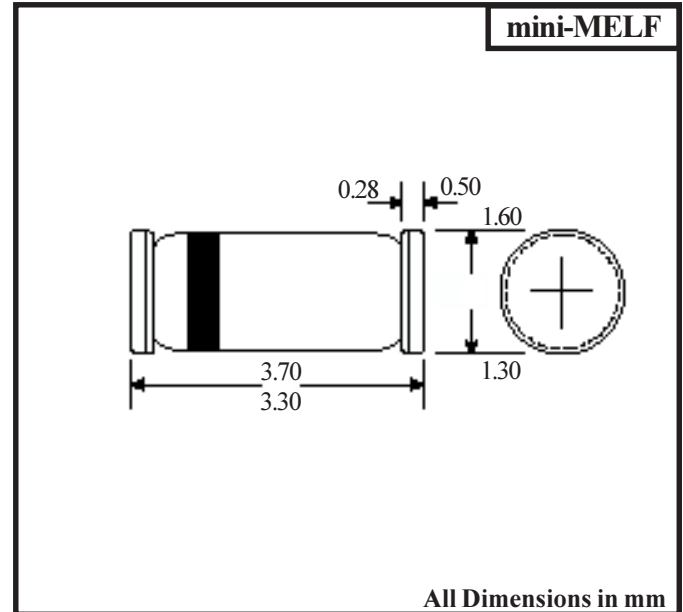
TECHNICAL SPECIFICATION

MM4448

1N4448 mini-MELF SIGNAL DIODE

Absolute Maximum Ratings (Ta = 25°C)

ITEMS	Symbol	Ratings	Unit
Peak Reverse Voltage	V_{RM}	100	V
Reverse Recovery Time	t_{rr}	4	ns
Power Dissipation	P	500	mW
Forward Current	I_{FM}	500 *	mA
Junction Temp.	T_J	(-65 to 175)	°C
Storage Temp.	T_{stg}	(-65 to 175)	°C



Mechanical Data

Items	Materials
Package	mini MELF
Case	Hermetically sealed glass
Lead/Finish	Double stud/Solder Plating
Chip	Glass Passivated

Ratings	Symbol	Ratings	Unit
Non-Repetive Peak Reverse Voltage	V_{RM}	100	V
Minimum Breakdown Voltage @ $I_R = 100\text{mA}$	B_V	75	V
Peak Forward Surge Current @ $t = 1.0\text{s}$	I_{FSM}	1 *	A
Forward Continuous Current	I_{FM}	500 *	mA
Maximum Forward Voltage $I_F = 100\text{mA}$	V_F	1	V
Maximum Reverse Current	I_R	25	nA
$V_R = 20\text{V}$		5	μA
$V_R = 75\text{V}$		30	μA
$V_R = 20\text{V}, T_j = 150\text{ }^\circ\text{C}$			
Maximum Junction Capacitance	Cj	4	pF
$V_R = 0, f = 1\text{ MHz}$			
Maximum Reverse Recovery Time	trr	4	ns
$I_F = 10\text{mA}, V_R = 6\text{V}, I_R = -1\text{mA}, R_L = 100\Omega$			
Maximum Thermal Resistance	$R_{\theta JA}$	300	K / W

* Note: Device terminals at ambient temperature